

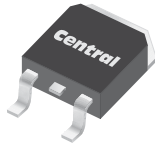
CJD340 NPN
CJD350 PNP

**SURFACE MOUNT
COMPLEMENTARY SILICON
POWER TRANSISTORS**



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**DPAK
POWER!**



DPAK TRANSISTOR CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD340, CJD350 types are Complementary Silicon Power Transistors manufactured in a surface mount package designed for high voltage general purpose applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Continuous Collector Current	I_C	500	mA
Peak Collector Current	I_{CM}	750	mA
Power Dissipation	P_D	15	W
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	1.56	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JC}	8.33	$^\circ\text{C/W}$
Thermal Resistance	θ_{JA}	80.1	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

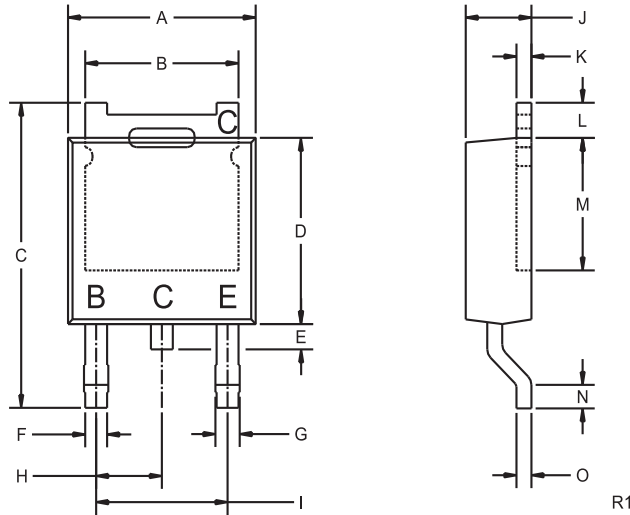
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CE}=300\text{V}$		100	μA
I_{EBO}	$V_{EB}=3.0\text{V}$		100	μA
BV_{CEO}	$I_C=1.0\text{mA}$	300		V
h_{FE}	$V_{CE}=10\text{V}, I_C=50\text{mA}$	30	240	

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DPAK TRANSISTOR CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.250	0.265	6.35	6.73
B	0.205	0.215	5.21	5.46
C	0.374	0.409	9.50	10.40
D	0.235	0.245	5.97	6.22
E	0.025	0.040	0.64	1.02
F	0.025	0.035	0.64	0.88
G	0.030	0.045	0.76	1.14
H	0.090		2.28	
I	0.180		4.57	
J	0.086	0.094	2.19	2.38
K	0.018	0.023	0.46	0.58
L	0.040	0.050	1.02	1.27
M	0.170	-	4.32	-
N	0.020	-	0.51	-
O	0.018	0.023	0.46	0.58

LEAD CODE:
B) BASE
C) COLLECTOR
E) EMITTER
C) COLLECTOR

MARKING:
FULL PART NUMBER

DPAK TRANSISTOR (REV: R1)

R2 (4-January 2010)